
HVM100

Silicon Epitaxial Planar Diode for High Voltage Switching

HITACHI

ADE-208-470 (Z)

Rev 0

September 1996

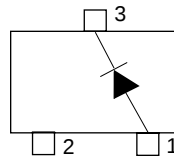
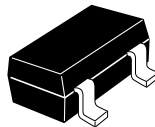
Features

- High capacitance ratio. ($n = 16.0$ min)
- High figure of merit. ($Q = 200$ min)
- To be usable at low voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVM100	T12	MPAK

Outline



(Top View)

- 1 Anode
- 2 NC
- 3 Cathode

HVM100

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	15	V
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-45~+125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	VR	15	~	~	V	IR = 10μA
Reverse current	IR	~	~	100	nA	VR =9V
Capacitance	C1	421.5	~	524.6	pF	VR = 1V, f = 1 MHz
	C5	73.2	~	121.4		VR = 5V, f = 1 MHz
	C8	20.4	~	28.2		VR = 8V, f = 1 MHz
Capacitance ratio	n	16	~	~	~	C1/ C8
Figure of merit	Q	200	~	~	~	C = 450pF, f = 1 MHz
ESD-Capability*1	~	80	~	~	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Failure criterion ; IR ≥ 100μA at VR =9 V

Main Characteristic

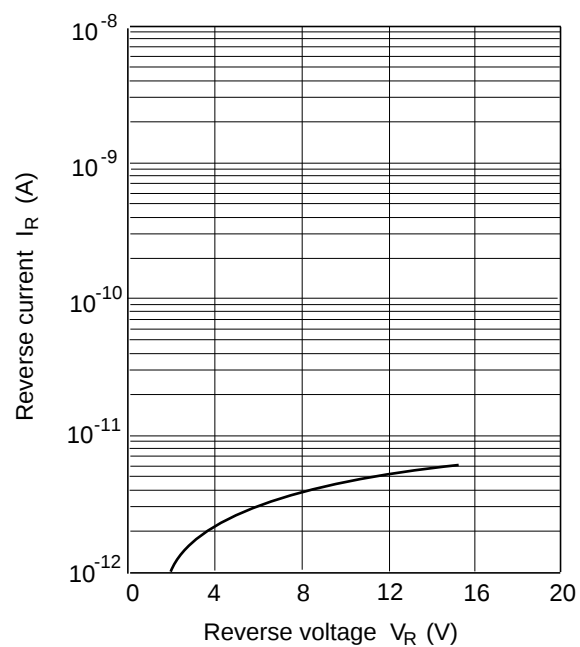


Fig.1 Reverse current Vs. Reverse voltage

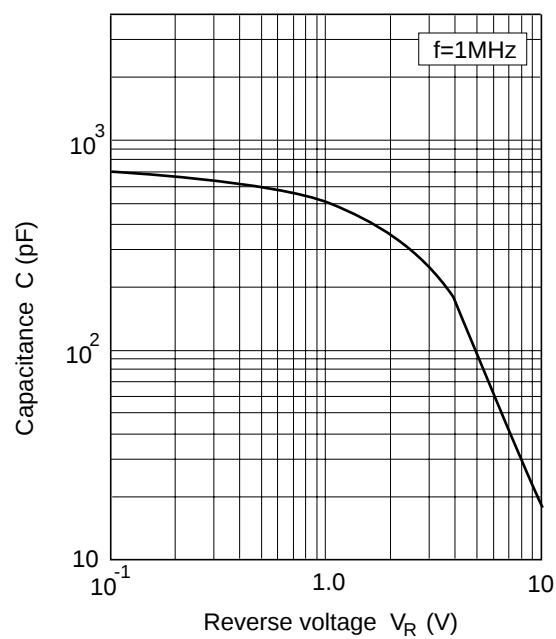


Fig.2 Capacitance Vs. Reverse voltage

